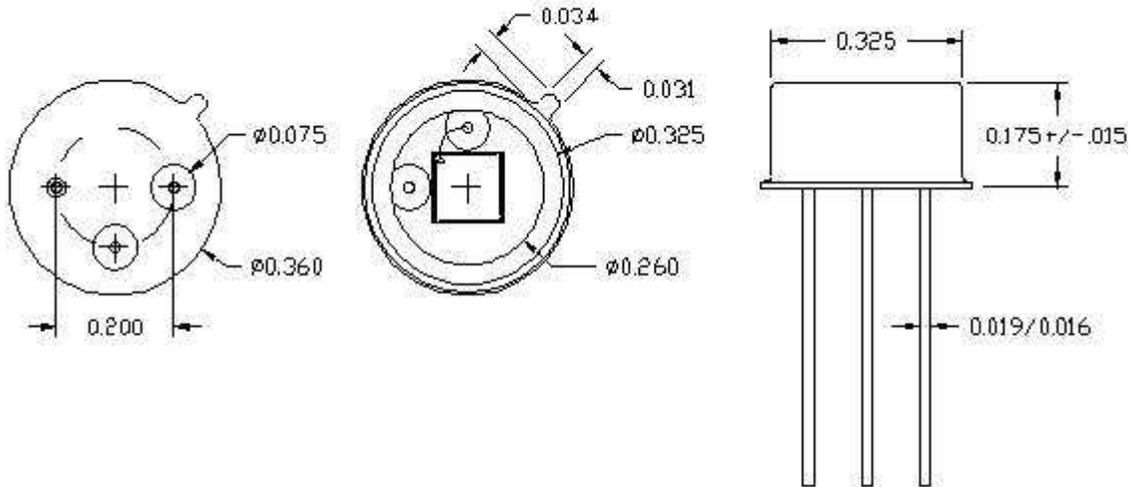


DESCRIPTION

This is a large area Silicon detector optimized for applications requiring high Responsivity and high reliability.

FEATURES

- High Speed and high Responsivity
- Large Active Area, 0.110" x 0.110" square
- High Reliability Hermetic TO-5 Package
- Similar to FFD-100 and TOX 9103 devices



ABSOLUTE MAXIMUM RATINGS

- Storage temperature..... -65°C to +125°C
- Case operating temperature..... -55°C to +100°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 45 Volts

OUTLINE DIMENSIONS

Tolerances are +/- 0.005 inches, except as noted

Pin 1 - Anode, Pin 2 Cathode, Pin 3 Case (Cathode)

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	$I_r = 30 \mu A, H = 0 \text{ mW}$	V_{BR}	45	240		Volts
Responsivity	$H = 10 \mu W, V_r = 5 \text{ Volts}$ $\lambda = 900 \text{ nm}$	R_c	.45	.55		A/W
Dark Current	$V_r = 20 \text{ Volts}, H = 0 \text{ mW}$	I_d		5	30	nA
Response Time	10%-90%, $V_r = 5 \text{ Volts}$ $R_c = 50 \Omega$	t_r t_f		5		nsec nsec
Spectral Response		λ	400		1100	nm
Capadance	$V_r = 5V, f = 1 \text{ MHz}$	C		17		pF
Forward Voltage	$I_f = 20 \text{ mA}$	V_f		0.9	1.1	Volts

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)